

**DL-3147-041**

Index Guided AlGaInP Laser Diode

Overview

DL-3147-041 is index guided 645 nm (Typ.) AlGaInP laser diode with low threshold current and high operating temperature. The low threshold current and high operating temperature are achieved by a strained multiple quantum well active layer. DL-3147-041 is suitable for applications such as bar-code reader, optical disc systems and other optical information systems.

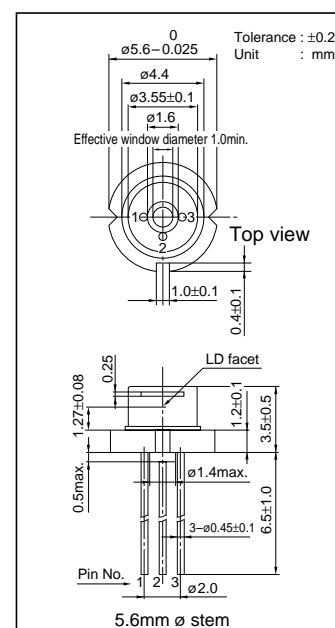
Features

- Short wavelength : 645 nm (Typ.)
- Low threshold current : $I_{th} = 45$ mA (Typ.)
- High operating temperature : 5 mW at 60°C
- TE mode

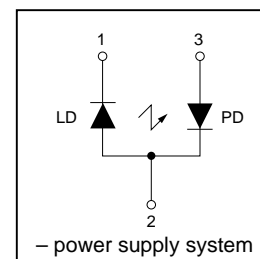
Absolute Maximum Ratings at $T_c=25^\circ\text{C}$

Parameter	Symbol	Ratings	Unit
Light Output	P_o	5	mW
Reverse Voltage	Laser PIN V_R	2	V
		30	
Operating Temperature	T_{opr}	-10 to +60	$^\circ\text{C}$
Storage Temperature	T_{stg}	-40 to +85	$^\circ\text{C}$

Package Dimensions



Electrical Connection



Electrical and Optical Characteristics at $T_c=25^\circ\text{C}$

Parameter		Symbol	Condition	Min.	Typ.	Max.	Unit
Threshold Current		Ith	CW	25	45	60	mA
Operating Current		Iop	Po=5mW	40	60	80	mA
Operating Voltage		Vop	Po=5mW	2.0	2.2	2.5	V
Lasing Wavelength		λ p	Po=5mW	635	645	655	nm
Beam \ast) Divergence	Perpendicular	$\theta \perp$	Po=5mW	25	30	40	deg.
	Parallel	$q //$	Po=5mW	7.0	7.5	10	deg.
Off Axis Angle	Perpendicular	$\Delta\theta \perp$	-	-	-	± 3	deg.
	Parallel	$\Delta\theta //$	-	-	-	± 2	deg.
Differential Efficiency		dPo/dIop	-	0.15	0.35	0.8	mW/mA
Monitoring Output Current		Im	Po=5mW	0.05	0.15	0.5	mA
Astigmatism		As	Po=5mW	-	8	-	mm

\ast) Full angle at half maximum note : The above product specifications are subject to change without notice.

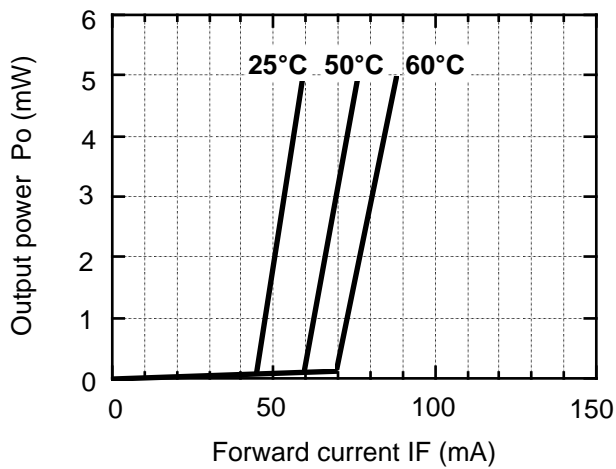
SANYO Electric Co.,Ltd. Semiconductor Business Headquarters

TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110-8534 JAPAN

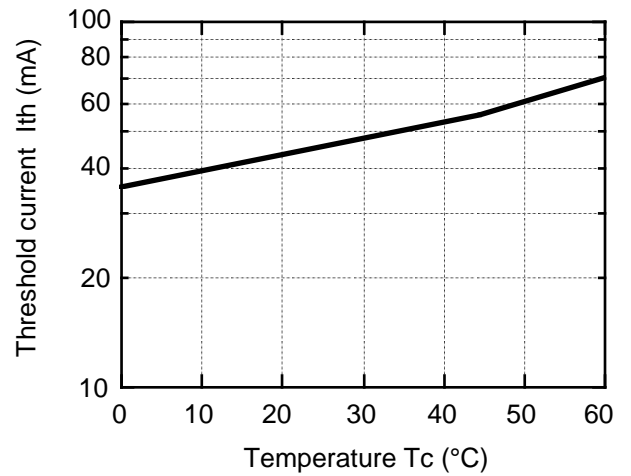
N2798 GI / N2897 GI, (IM) No.5862 1/3

Characteristics

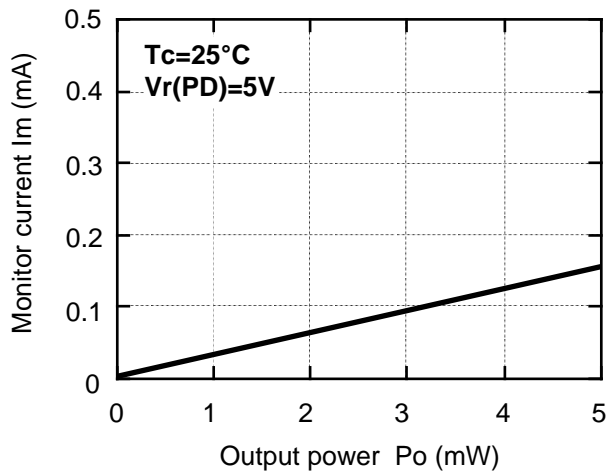
Output power vs. Forward current



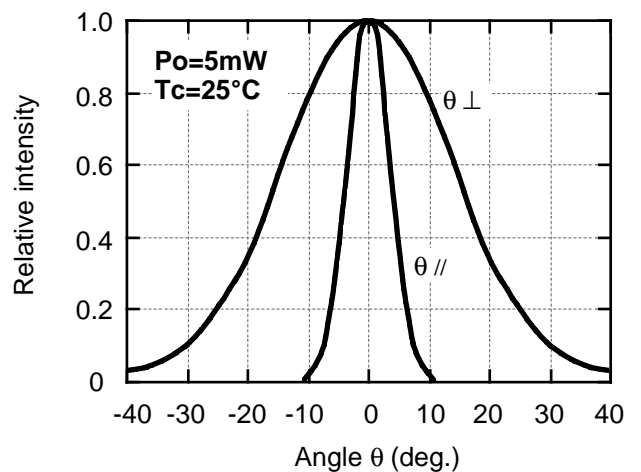
Threshold current vs. Temperature



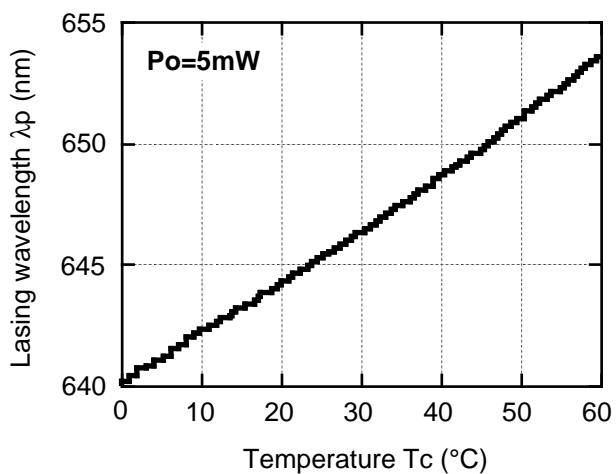
Monitor current vs. Output power



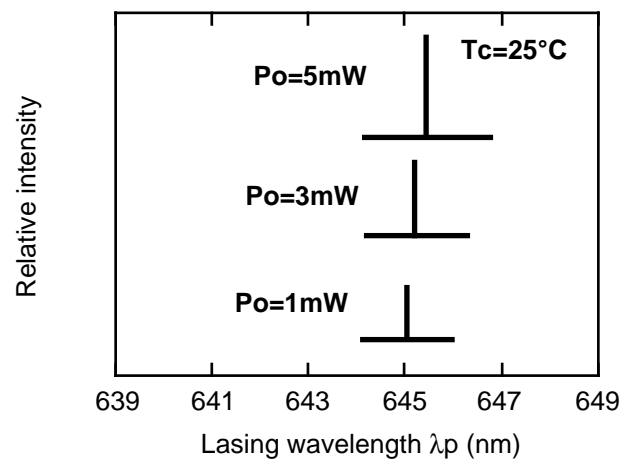
Beam divergence



Lasing wavelength vs. Temperature



Output power vs. Lasing wavelength





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Precautionary instructions in handling gallium arsenic products

Special precautions must be taken in handling this product because it contains, gallium arsenic, which is designated as a toxic substance by law. Be sure to adhere strictly to all applicable laws and regulations enacted for this substance, particularly when it comes to disposal.

Manufactured by ; **Tottori SANYO Electric Co., Ltd.**
Electronics Device Bussiness Headquarters LED Division
5-318, Tachikawa-cho, Tottori City, 680-8634 Japan
TEL: +81-857-21-2137 FAX: +81-857-21-2161